

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1	"10/780171".app.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/17 07:34
S2	6	("5640343") or ("6317375") or ("6356477")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/21 08:39
S3	612	(word adj line) (bit adj line) (pinned adj layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/29 07:49
S4	5	(global adj word adj line) (bit adj line) (pinned adj layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/29 09:40
S5	424	(global adj word adj line) (bit adj line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/29 09:43
S6	5	"6879505"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/29 11:48
S7	981	(MRAM or magnetic) adj (RAM or memory) adj4 array	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/29 11:49
S8	424	(global adj word adj line) (bit adj line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/29 11:49

S10	6	S7 S8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/29 11:52
S11	44376	(word adj line) (bit adj line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/29 11:53
S12	464	S7 S11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/29 11:53
S13	449	S7 S11 (switch\$3 or select\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/29 11:53
S14	253	S7 S11 (switch\$3 or select\$3) (MTJ or (magnetic adj tunnel\$3 adj junction))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/29 11:54
S15	247	S7 S11 (switch\$3 or select\$3) (MTJ or (magnetic adj tunnel\$3 adj junction)) (layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/29 11:55
S16	98	S7 S11 (switch\$3 or select\$3) (MTJ or (magnetic adj tunnel\$3 adj junction)) (diode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/09/29 12:34
S18	80	(LIN-WEN-CHI LIN-WEN-CHIANG-H LIN-WEN-CHIEH LIN-WEN-CHIEN LIN-WEN-CHIH LIN-WEN-CHIN LIN-WEN-CHUAN LIN-WEN-CHUN LIN-WEN-CHUNG LIN-WEN-CHYI LIN-WEN-DON).in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 08:44

S20	1	S18 global adj2 line	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/14 08:45
S21	102	global adj3 line (word adj line) (bit adj line) (MRAM)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/14 08:45
S22	64	global adj3 line (word adj line) (bit adj line) (MRAM) (MTJ)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/14 08:45
S23	42	S22 (switch)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/14 10:08
S24	11	S23 segment	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/14 10:08
S25	17	S23 segment\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/14 12:04
S26	412	(global or main) adj2 (((bit or data) and word) adj line) or ((bitline or dataline) and wordline))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/14 12:06
S27	1884	((diode and transistor) adj2 switch)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/17 07:34

S28	340	((diode and transistor) adj2 switch) memor\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/17 07:38
S29	4	((diode and transistor) adj2 switch) memor\$3 MTJ	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/17 07:35
S30	18	((diode and transistor) adj2 switch) memor\$3 NMOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/17 07:42
S31	1619	(diode transistor) memor\$3 NMOS word adj line	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/17 07:42
S32	1243	(diode transistor) memor\$3 NMOS word adj line bit adj line	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/17 09:28
S34	15	(super adj diode) memor\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/17 09:29
S35	1904	diode near5 replac\$3 near5 transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/17 09:30
S36	489	(diode near5 replac\$3 near5 transistor) memor\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/17 09:30

S37	157	(diode near5 replac\$3 near5 transistor) memor\$3 ("365".clas.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/17 09:30
S38	1558	(365/171).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/17 14:04
S39	24	S38 ((main or global) adj ((word adj line) or wordline))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/17 14:04
S40	3585	(365/230.03).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/17 14:04
S41	379	S40 ((main or global) adj ((word adj line) or wordline))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/17 14:05
S42	44	S40 ((main or global) adj ((word adj line) or wordline)) ((main or global) adj ((bit adj line) or bitline))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/17 14:05
S43	4	S42 MTJ	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/17 14:05
S44	6	S42 (((magnetic or magneto) adj tunnel\$4 adj junction) or MTJ)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/17 14:07